



**S3AC-S3MC**

**Feature**

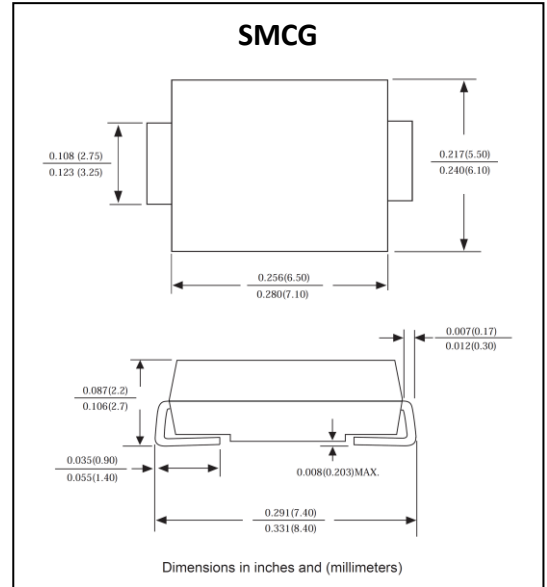
- I<sub>o</sub> 3A
- V<sub>RRM</sub> 50V-1000V
- Glass passivated chip
- High surge current capability

**Application**

- Rectifier

**Marking**

- S3X X: From A to M



**ABSOLUTE MAXIMUM RATINGS (T<sub>a</sub>=25°C unless otherwise noted)**

Parameter	Symbol	S3							Unit
		A	B	D	G	J	K	M	
Repetitive Peak Reverse Voltage	V <sub>RRM</sub>	50	100	200	400	600	800	1000	V
Maximum RMS Voltage	V <sub>RMS</sub>	35	70	140	280	420	560	700	V
Average Forward Current 60HZ Half-sine wave, Resistance load, T <sub>L</sub> =110°C	I <sub>F(AV)</sub>	3							A
Non-repetitive Peak Forward Surge Current 60Hz Half-sine wave ,1 cycle ,T <sub>a</sub> =25°C	I <sub>FSM</sub>	100							A
Junction Temperature	T <sub>J</sub>	-55 ~ +150							°C
Storage Temperature	T <sub>STG</sub>	-55 ~ +150							°C

**ELECTRICAL CHARACTERISTICS (T<sub>a</sub>=25°C unless otherwise noted)**

Parameter	Symbol	Test Condition	S3							Unit
			A	B	D	G	J	K	M	
Peak Forward Voltage	V <sub>F</sub>	I <sub>F</sub> =3A	1.15							V
Typical reverse recovery time	t <sub>rr</sub>	I <sub>F</sub> =0.5A, I <sub>R</sub> =1.0A, I <sub>rr</sub> =0.25A	2.5							us
Peak Reverse Current	I <sub>RRM1</sub>	V <sub>RM</sub> =V <sub>R</sub> T <sub>a</sub> =25°C	10							uA
	I <sub>RRM2</sub>	V <sub>RM</sub> =V <sub>R</sub> T <sub>a</sub> =125°C	250							uA
Thermal Resistance(Typical)	R <sub>θJ-A</sub>	Between junction and ambient	47							°C/W
	R <sub>θJ-L</sub>	Between junction and terminal	10							°C/W

**Typical Characteristics**

FIG.1: FORWARD CURRENT DERATING CURVE

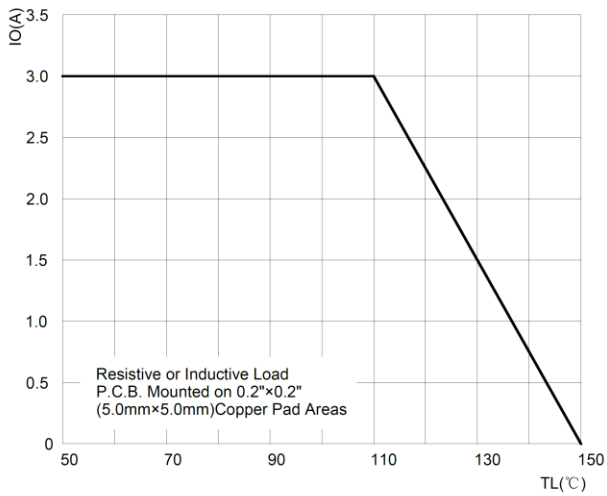


FIG.2: MAXIMUM NON-REPETITIVE FORWARD URGE CURRENT

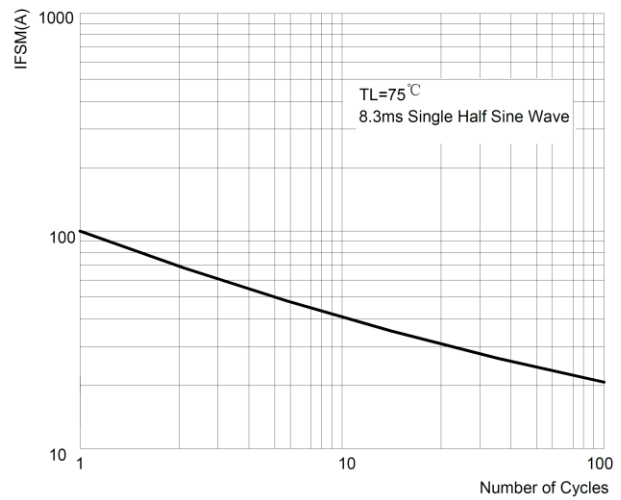


FIG.3: TYPICAL FORWARD CHARACTERISTICS

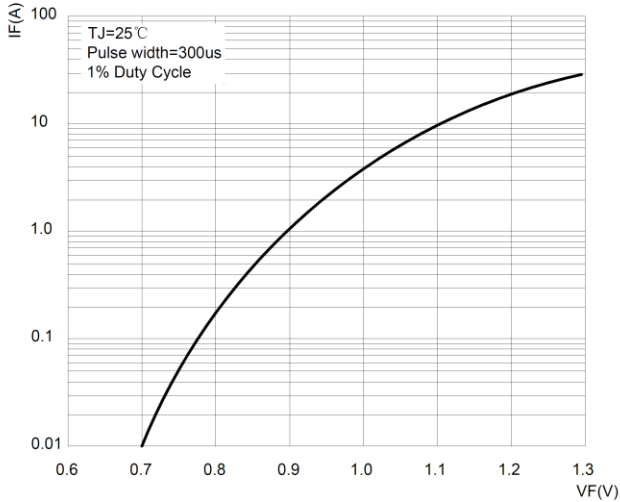


FIG.4: TYPICAL REVERSE CHARACTERISTICS

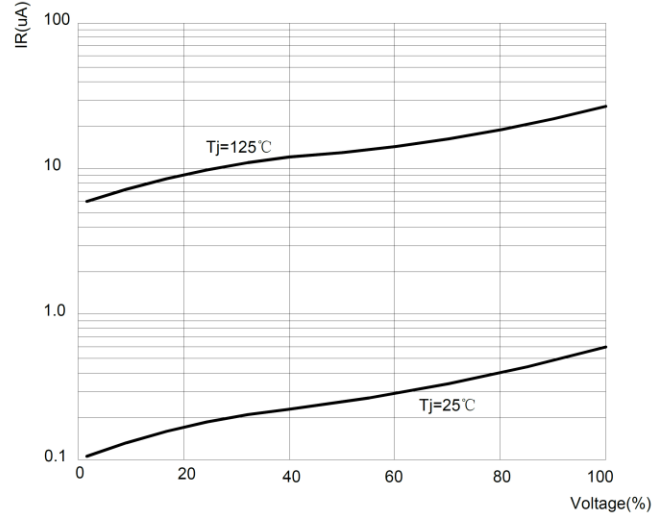


FIG.5: Diagram of circuit and Testing wave form of reverse recovery time

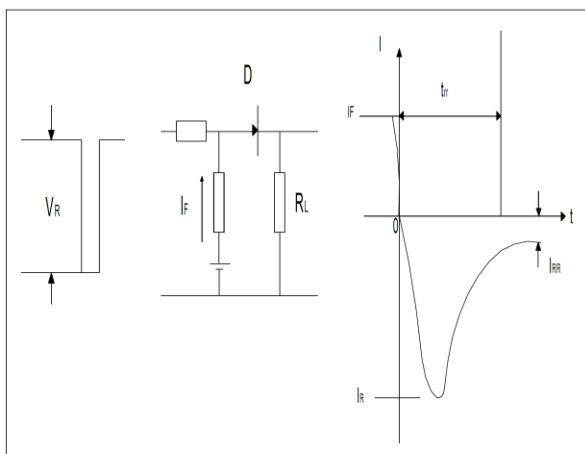
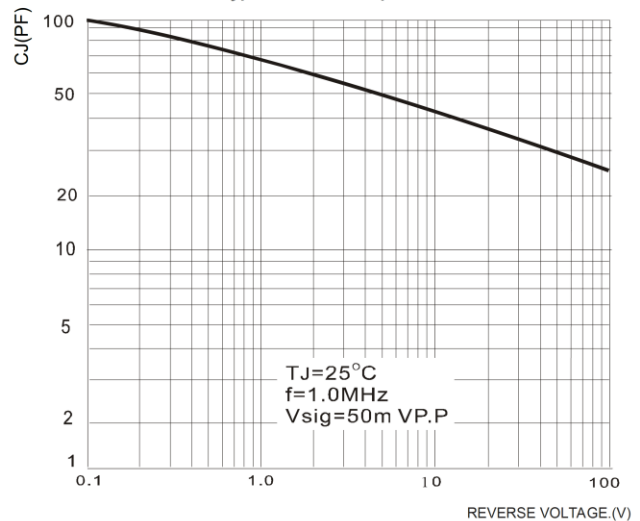


FIG6: Typical Junction Capacitance



单击下面可查看定价，库存，交付和生命周期等信息

[>>GP\(格瑞宝\)](#)